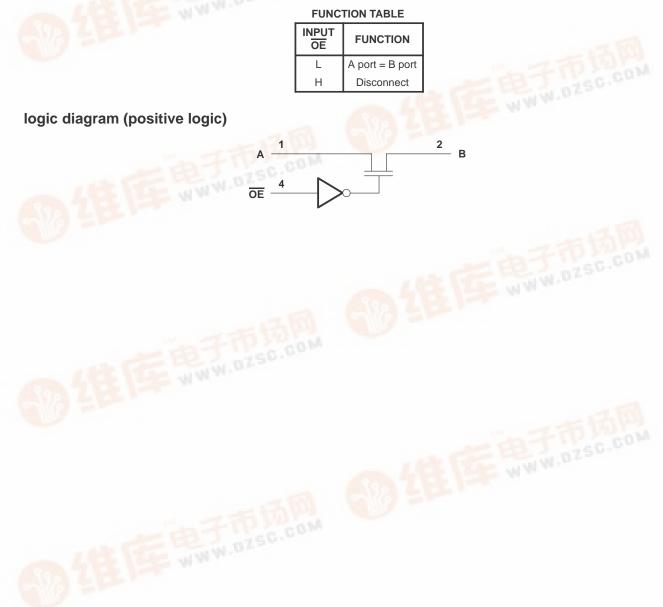


The SN74CBT1G384 features a single high-speed line switch. The switch is disabled when the output-enable (OE) input is high.

The SN74CBT1G384 is characterized for operation from -40°C to 85°C.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



SN74CBT1G384 SINGLE FET BUS SWITCH

SCDS065B – JULY 1998 – REVISED JANUARY 2000

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC} Input voltage range, V _I (see Note 1)	
Continuous channel current	
Input clamp current, I _{IK} (V _{I/O} < 0)	–50 mA
Package thermal impedance, θ_{JA} (see Note 2): DBV package	347°C/W
DCK package	389°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 3)

		MIN	MAX	UNIT
VCC	Supply voltage	4	5.5	V
VIH	High-level control input voltage	2		V
VIL	Low-level control input voltage		0.8	V
Т _А	Operating free-air temperature	-40	85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

P/	PARAMETER TEST CONDITIONS			MIN	TYP [‡]	MAX	UNIT		
VIK		V _{CC} = 4.5 V,	Ij = -18 mA					-1.2	V
Ц		V _{CC} = 5.5 V,	$V_I = 5.5 V \text{ or GND}$					±1	μA
ICC		V _{CC} = 5.5 V,	I _O = 0,	$V_{I} = V_{CC} \text{ or } GN$	D			1	μA
Ci	Control input	$V_{I} = 3 V \text{ or } 0$					3		pF
C _{io(OF}	FF)	V _O = 3 V or 0,	$OE = V_{CC}$				4		pF
r _{on} §		$V_{CC} = 4 V,$	TYP at $V_{CC} = 4 V$,	$V_{ } = 2.4 V_{, }$	l _l = 15 mA		14	20	
			$V_{I} = 0$	l _l = 64 mA			5	7	Ω
		$V_{CC} = 4.5 V$	/ _{CC} = 4.5 V	I _I = 30 mA			5	7	52
			V _I = 2.4 V,	lj = 15 mA			10	15	

[‡] All typical values are at $V_{CC} = 5 V$ (unless otherwise noted), $T_A = 25^{\circ}C$.

S Measured by the voltage drop between the A and the B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

switching characteristics over recommended operating free-air temperature range, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 1)

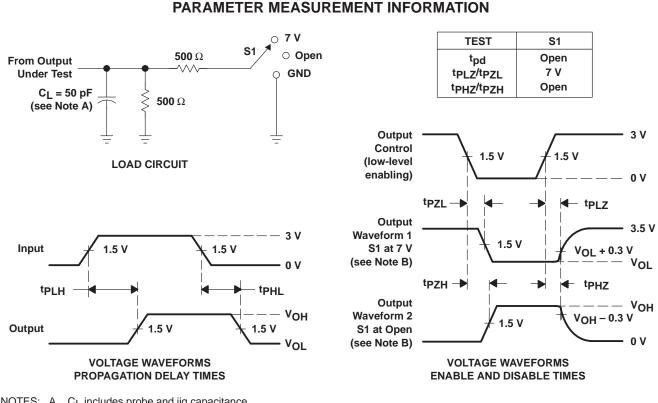
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 4 V	V _{CC} = 5 V ± 0.5 V		UNIT
			MIN MAX	MIN	MAX	
t _{pd} ¶	A or B	B or A	0.35		0.25	ns
t _{en}	OE	A or B	5.5	1.6	4.9	ns
^t dis	OE	A or B	4.5	1	4.2	ns

The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).



SN74CBT1G384 SINGLE FET BUS SWITCH

SCDS065B - JULY 1998 - REVISED JANUARY 2000



NOTES: A. CL includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_Q = 50 Ω , t_f \leq 2.5 ns, t_f \leq 2.5 ns.
- D. The output is measured with one input transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tPLH and tPHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 2000, Texas Instruments Incorporated